

FACULTY OF ENGINEERING

B.E. (I.T.) 4/4 I - Semester (Old) Examination, May / June 2019

Subject : VLSI Design

Time : 3 Hours

Max. Marks: 75

Note: Answer all questions from Part-A & any five questions from Part-B.

PART – A (25 Marks)

- 1 Explain how a MOSFET works as a switch. (3)
- 2 Explain the operation of transmission gate logic. (3)
- 3 Draw the CMOS diagram of xor gate. (2)
- 4 Write about the layers used to create MOSFET. (2)
- 5 Write in brief about the stick diagrams? (3)
- 6 Explain Cell concepts briefly. (2)
- 7 Explain with a diagram Tri State circuit. (3)
- 8 What is propagation delay and write the expression for the same. (3)
- 9 Write the verilog code of half adder. (2)
- 10 Write in brief about testing. (2)

PART – B (50 Marks)

- 11 (a) Illustrate bubble pushing using De Morgan's Law. (5)
- (b) Draw the CMOS diagram of XOR and XNOR logic gate and explain with a truth table. (5)
- 12 (a) Draw the layout of three input NAND. (5)
- (b) Write about photolithography. (5)
- 13 (a) Draw the DC characteristics of CMOS inverter and find the midpoint voltage. (4)
- (b) With a neat diagram explain CMOS process flow for fabrication. (6)
- 14 (a) Explain read and write operation of DRAM cell. (5)
- (b) Write about effect of charge storage on floating gate. (5)
- 15 (a) What is an interconnect? Derive the delay modeling of an interconnect. (5)
- (b) Write the verilog code for full adder. (5)
- 16 (a) Design a 4 bit barrel shifter. (5)
- (b) Write about multipliers. (5)
- 17 (a) Design an 8:1 MUX using 2:1MUX transmission gates. (5)
- (b) Write about RTL and Behavioral modelling. (5)
